

August 2014

FDA16N50LDTU N-Channel UniFETTM MOSFET 500 V, 16.5 A, 380 m Ω

Features

- $R_{DS(on)}$ = 310 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 8.3 A
- Low Gate Charge (Typ. 32 nC)
- Low C_{rss} (Typ. 20 pF)
- · 100% Avalanche Tested
- · RoHS Compliant

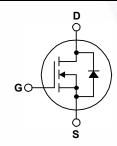
Applications

- PDP TV
- · Uninterruptible Power Supply

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter			Unit	
V_{DSS}	Drain to Source Voltage	Orain to Source Voltage			V	
V_{GSS}	Gate to Source Voltage			±30	V	
	Drain Current	- Continuous (T _C = 25°C)		16.5	А	
ID	Diain Current	- Continuous (T _C = 100°C)		9.9		
I _{DM}	Drain Current	- Pulsed	- Pulsed (Note 1)		Α	
E _{AS}	Single Pulsed Avalanche Energy (Note 2)			780	mJ	
I _{AR}	Avalanche Current (Note 1)		(Note 1)	16.5	Α	
E _{AR}	Repetitive Avalanche Energy (Note 1)		(Note 1)	20.5	mJ	
dv/dt	Peak Diode Recovery dv/	/dt	(Note 3)	4.5	V/ns	
D	Dower Dissinction	(T _C = 25°C)		205	W	
P_{D}	Power Dissipation	- Derate Above 25°C		2.1	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range			-55 to +150	°C	
T _L	Maximum Lead Tempera	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds			°C	

Thermal Characteristics

Symbol	Parameter	FDA16N50LDTU	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.6	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	40	-0/00

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDA16N50LDTU	FDA16N50	TO-3PN (L-forming)	Tube	N/A	N/A	30 units

Electrical Characteristics T_C = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V, T_J = 25^{\circ} C$	500	-	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C	-	0.50	-	V/°C
	Zero Gate Voltage Drain Current	V _{DS} = 500 V, V _{GS} = 0 V	-	-	20	μА
DSS	Zero Gate Voltage Drain Current	$V_{DS} = 500 \text{ V}, T_{C} = 125^{\circ}\text{C}$	-	-	200	μΑ
I _{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	±100	nA

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu\text{A}$	3.0	-	5.0	V
R _{DS(on)}	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 8.3 \text{ A}$	-	0.31	0.38	Ω
9 _{FS}	Forward Transconductance	$V_{DS} = 40 \text{ V}, I_{D} = 8.3 \text{ A}$	ı	23	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V - 25 V V - 0 V	-	1495	1945	pF
Coss	Output Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ $V_{DS} = 1 \text{ MHz}$	- \	235	310	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1 1011 12	-	20	30	pF
Q _{g(tot)}	Total Gate Charge at 10V	V _{DS} = 400 V, I _D = 16 A,	-	32	45	nC
Q_{gs}	Gate to Source Gate Charge	V _{GS} = 10 V	-	8.5	-	nC
Q_{gd}	Gate to Drain "Miller" Charge	(Note 4)	-	14	-	nC

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		-	40	90	ns
t _r		$V_{DD} = 250 \text{ V}, I_D = 16 \text{ A},$	-	150	310	ns
t _{d(off)}	Turn-Off Delay Time	V_{GS} = 10 V, R_G = 25 Ω	-	65	140	ns
t _f	Turn-Off Fall Time	(Note 4)	-	80	170	ns

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	16.5	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	66	Α
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 16.5 A	-	-	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 16 A,	-	490	/ -	ns
Q _{rr}	Reverse Recovery Charge	dI _F /dt = 100 A/μs	-	5.0	-	μС

Notes

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. L = 5.1 mH, I $_{AS}$ = 16.5 A, V $_{DD}$ = 50 V, R $_{G}$ = 25 $\Omega,$ starting T $_{J}$ = 25 $^{\circ}C.$
- 3. I_{SD} \leq 16.5 A, di/dt \leq 200 A/µs, V_{DD} \leq BV_DSS, starting T_J = 25°C.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

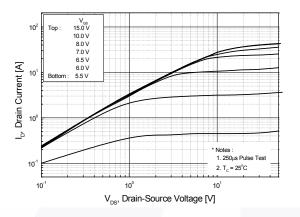


Figure 2. Transfer Characteristics

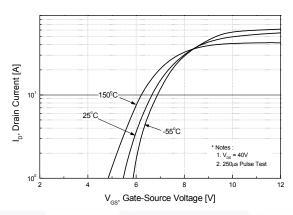
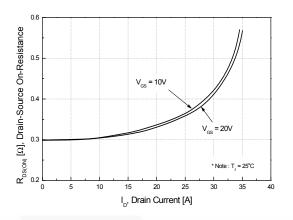


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage





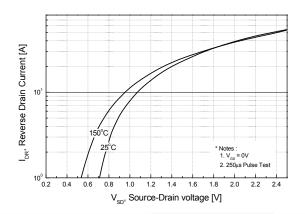


Figure 5. Capacitance Characteristics

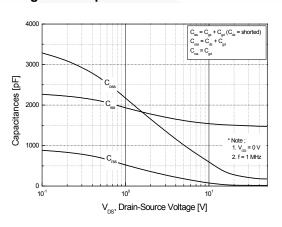
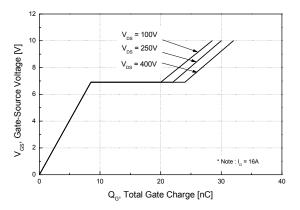


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

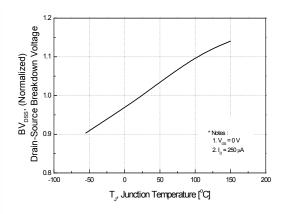


Figure 8. On-Resistance Variation vs. Temperature

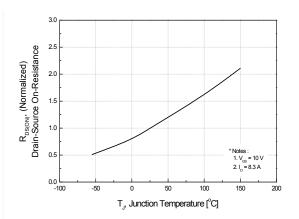
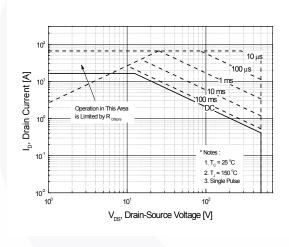


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature



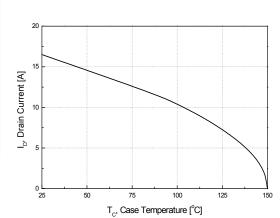
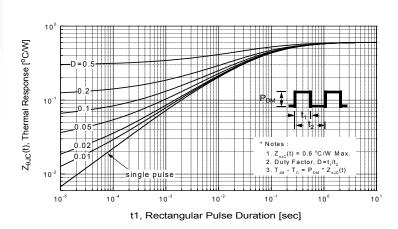


Figure 11. Transient Thermal Response Curve



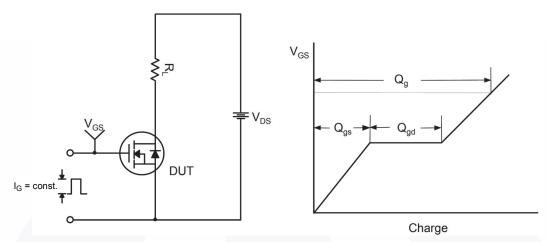


Figure 12. Gate Charge Test Circuit & Waveform

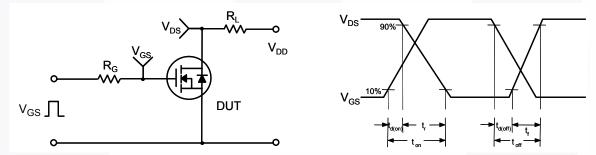


Figure 13. Resistive Switching Test Circuit & Waveforms

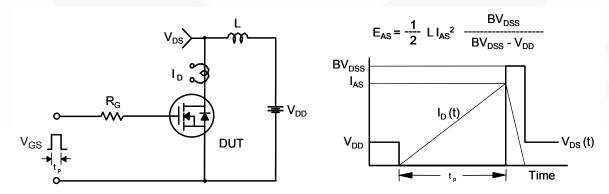


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

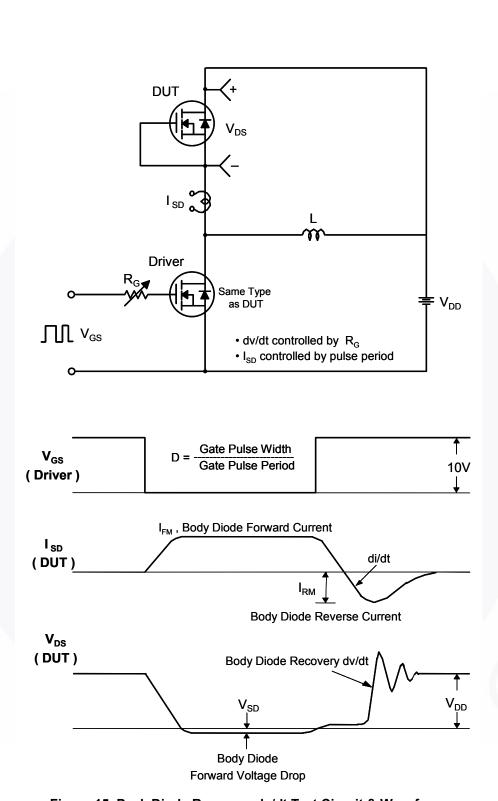
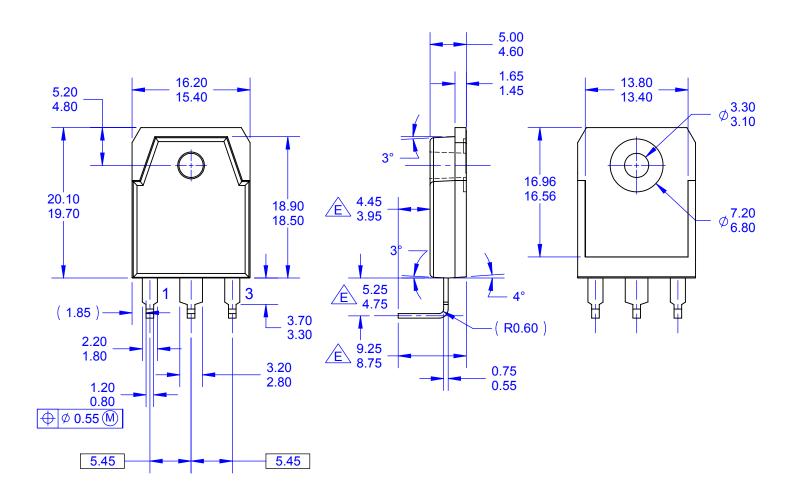
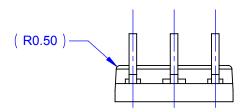


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms





NOTES: UNLESS OTHERWISE SPECIFIED

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- B) ALL DIMENSIONS ARE IN MILLIMETERS.
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- ASME14.5-2009.
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